

Dual NPN Bias Resistor Transistors R1 = 22 k Ω , R2 = 47 k Ω

NPN Transistors with Monolithic Bias Resistor Network

MUN5234DW1, NSBC124XDXV6

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

(T_A = 25°C, common for Q₁ and Q₂, unless otherwise noted)

Symbol	Rating	Max	Unit
V _{CBO}	Collector-Base Voltage	50	Vdc
V _{CEO}	Collector-Emitter Voltage	50	Vdc
I _C	Collector Current - Continuous	100	mAdc
V _{IN(fwd)}	Input Forward Voltage	40	Vdc
V _{IN(rev)}	Input Reverse Voltage	7	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

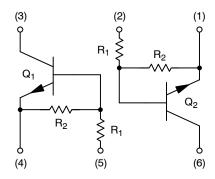


SOT-363 CASE 419B

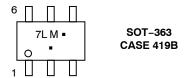


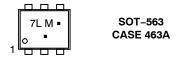
SOT-563 CASE 463A

PIN CONNECTIONS



MARKING DIAGRAMS





7L = Specific Device Code
M = Date Code*

Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MUN5234DW1T1G	SOT-363	3,000 / Tape & Reel
NSBC124XDXV6T1G	SOT-563	4,000 / Tape & Reel
NSVBC124XDXV6T1G	SOT-563	4,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MUN5234DW1, NSBC124XDXV6

THERMAL CHARACTERISTICS

Symbol		Characteristic	Max	Unit
MUN5234DW	(SOT-363) ONE JUNCTION H	EATED		
P _D	Total Device Dissipation $T_A = 25^{\circ}C \qquad \text{(Note 1)}$ (Note 2) Derate above 25°C (Note 2)	(Note 1)	187 256 1.5 2.0	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	670 490	°C/W
MUN5234DW1	(SOT-363) BOTH JUNCTION I	HEATED (Note 3)		
P_{D}	Total Device Dissipation $T_A = 25^{\circ}C \qquad \text{(Note 1)}$ (Note 2) Derate above 25°C (Note 2)	(Note 1)	250 385 2.0 3.0	mW mW/°C
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (Note 2)	(Note 1)	493 325	°C/W
$R_{ hetaJL}$	Thermal Resistance, Junction to Lead (Note 1) (Note 2)		188 208	°C/W
T _J , T _{stg}	Junction and Storage Temper	ature Range	-55 to +150	°C
NSBC124XDX	V6 (SOT-563) ONE JUNCTION	HEATED		
P _D	Total Device Dissipation T _A = 25°C (Note 1) Derate above 25°C	(Note 1)	357 2.9	mW mW/°C
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient	(Note 1)	350	°C/W
NSBC124XDX	V6 (SOT-563) BOTH JUNCTION	N HEATED (Note 3)		
P _D	Total Device Dissipation T _A = 25°C (Note 1) Derate above 25°C	(Note 1)	500 4.0	mW mW/°C
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	(Note 1)	250	°C/W
T _J , T _{stg}	Junction and Storage Temper	ature Range	-55 to +150	°C

FR-4 @ Minimum Pad.
 FR-4 @ 1.0 x 1.0 Inch Pad.
 Both junction heated values assume total power is sum of two equally powered channels.

MUN5234DW1, NSBC124XDXV6

ELECTRICAL CHARACTERISTICS (T_A = 25°C, common for Q₁ and Q₂, unless otherwise noted)

Symbol	Characteristic	Min	Тур	Max	Unit
OFF CHAR	ACTERISTICS	•	•		
I _{CBO}	Collector-Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_{E} = 0)$	-	-	100	nAdc
I _{CEO}	Collector-Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	-	-	500	nAdc
I _{EBO}	Emitter-Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_{C} = 0)$	-	-	0.13	mAdc
V _{(BR)CBO}	Collector-Base Breakdown Voltage ($I_C = 10 \mu A$, $I_E = 0$)	50	-	-	Vdc
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage (Note 4) $(I_C = 2.0 \text{ mA}, I_B = 0)$	50	-	-	Vdc
ON CHARA	CTERISTICS				
h _{FE}	DC Current Gain (Note 4) (I _C = 5.0 mA, V _{CE} = 10 V)	80	150	-	
V _{CE(sat)}	Collector-Emitter Saturation Voltage (Note 4) (I _C = 10 mA, I _B = 1.0 mA)	-	-	0.25	V
$V_{i(off)}$	Input Voltage (Off) $(V_{CE} = 5.0 \text{ V, I}_{C} = 100 \mu\text{A})$	-	0.8	-	Vdc
V _{i(on)}	Input Voltage (On) $(V_{CE} = 0.2 \text{ V, I}_{C} = 3.0 \text{ mA})$	-	1.3	-	Vdc
V _{OL}	Output Voltage (On) (V_{CC} = 5.0 V, V_{B} = 2.5 V, R_{L} = 1.0 k Ω)	-	-	0.2	Vdc
V _{OH}	Output Voltage (Off) (V_{CC} = 5.0 V, V_{B} = 0.5 V, P_{L} = 1.0 k Ω)	4.9	-	-	Vdc
R1	Input Resistor	15.4	22	28.6	kΩ
R ₁ /R ₂	Resistor Ratio	0.38	0.47	0.56	

^{4.} Pulsed Condition: Pulse Width = 300 ms, Duty Cycle ≤ 2%.

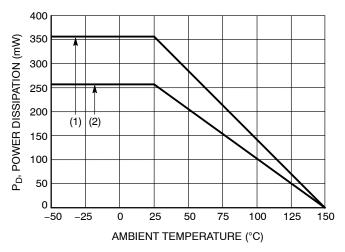


Figure 1. Derating Curve

(1) SOT–363; 1.0×1.0 Inch Pad (2) SOT–563; Minimum Pad

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MUN5234DW1, NSBC124XDXV6

TYPICAL CHARACTERISTICS MUN5234DW1, NSBC124XDXV6

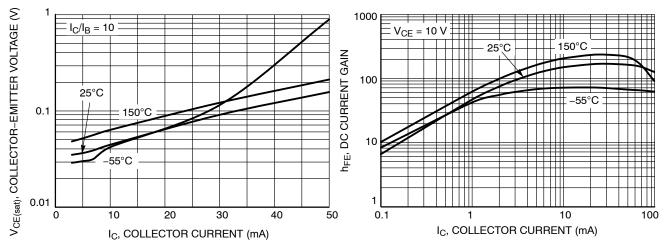


Figure 2. V_{CE(sat)} vs. I_C

Figure 3. DC Current Gain

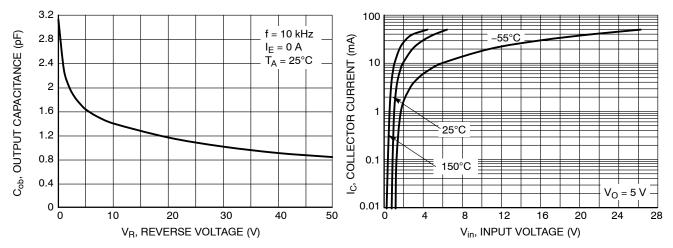


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

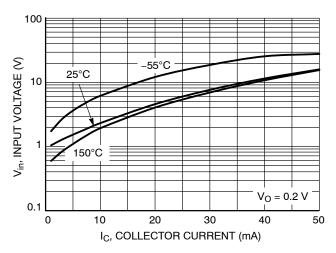


Figure 6. Input Voltage vs. Output Current





E1

6X 0.30 -

e

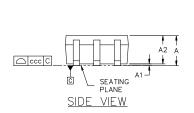
В

SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 **ISSUE Z**

DATE 18 APR 2024

NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
- DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 DATUMS A AND B ARE DETERMINED AT DATUM H.
- DIMENSIONS 6 AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. 6.
- DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.



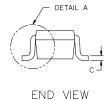
TOP VIEW

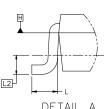
∆aaa H A−B

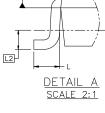
<u></u> БЬБ С

⊕ ddd M C A−B D

6X 0.66







2.50

RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code* = Pb-Free Package

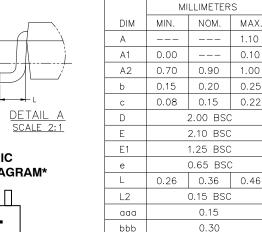
(Note: Microdot may be in either location)

- *Date Code orientation and/or position may vary depending upon manufacturing location.
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DESCRIPTION:	SC-88 2.00x1.25x0.90, 0.65	5P	PAGE 1 OF 2	

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ccc ddd 0.10

0.10

SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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STYLE 4:

STYLE 10:

5. N/C

PIN 1. COLLECTOR 2. COLLECTOR

3. BASE

4. EMITTER
5. COLLECTOR
6. COLLECTOR

SOT-563-6 1.60x1.20x0.55, 0.50P CASE 463A **ISSUE J**

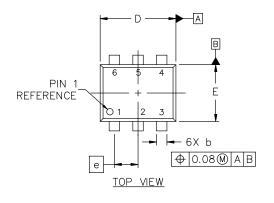
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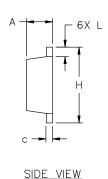
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- ALL DIMENSION ARE IN MILLIMETERS.

DIM

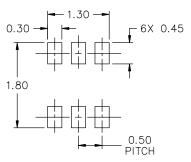
MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.





NDM. MIN. MAX. 0.50 0.55 0.60 Α b 0.17 0.22 0.27 \subset 0.08 0.13 0.18 D 1.50 1.60 1.70 Ε 1.10 1.20 1.30 9 0.50 BSC Н 1.50 1.60 1.70 0.20 0.30 L 0.10

MILLIMETERS



STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. EMITTER 1	PIN 1. EMITTER 1	PIN 1. CATHODE 1
2. BASE 1	2. EMITTER 2	2. CATHODE 1
3. COLLECTOR 2	3. BASE 2	3. ANODE/ANODE 2
4. EMITTER 2	4. COLLECTOR 2	4. CATHODE 2
5. BASE 2	5. BASE 1	5. CATHODE 2
6. COLLECTOR 1	6. COLLECTOR 1	6. ANODE/ANODE 1

RECOMMENDED	MOUNTING	FOOTPRINT*

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STYLE 7: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. ANODE 6. CATHODE	STYLE 8: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SDURCE 5. DRAIN 6. DRAIN	STYLE 9: PIN 1. SDURCE 1 2. GATE 1 3. DRAIN 2 4. SDURCE 2 5. GATE 2 6. DRAIN 1
6. CATHUDE	6. DRAIN	6. DRAIN 1

STYLE 11:

STYLE 5

3. ANDDE

PIN 1. CATHODE 2. CATHODE

4. ANDDE 5. CATHODE

6. CATHODE

GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Month Code

= Pb-Free Package *This information is generic. Please refer to device data sheet for actual part marking.

PIN 1. CATHODE 1 PIN 1. EMITTER 2 2. N/C 3. CATHODE 2 2. BASE 2 3. COLLECTOR 1 Pb-Free indicator, "G" or microdot "•", may 4. ANDDE 2 4. EMITTER 1 or may not be present. Some products may BASE 5. BASE 1 6. COLLECTOR 2 not follow the Generic Marking. 6. AN□DE 1

STYLE 6: PIN 1. CATHODE 2. ANODE

CATHODE

CATHODE

4. CATHODE 5. CATHODE

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